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Unveiling exceptional valley contrast in AA- and AB-stacked bilayer WS₂

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Yanlong Wang,^{a,b} Chunxiao Cong,^{*c} Jingzhi Shang,^a Mustafa Eginligil,^d Yuqi Jin,^b Gang Li,^b Yu Chen,^a Namphung Peimyoo,^a and Ting Yu^{*a}

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Valleytronics is a particularly interesting field that employs the valley degree of freedom for information manipulation. The fascinating prospects to realize valleytronic devices have inspired persistent efforts to explore the material systems with robust valley polarization. Monolayer transition metal dichalcogenides (TMDs) possess the well-known valley-dependent selection rule as a result of the inversion asymmetry. However, for inversion-symmetric bilayer tungsten-based TMDs, the highly selective valley polarization has been surprisingly observed and is not yet fully understood. Here we systematically study the origin of the anomalously high valley polarization in bilayer WS₂ by temperature-dependent polarization-resolved photoluminescence measurements. It is found that the acoustic phonons play a critical role in the valley polarization of bilayer WS₂. For some WS₂ bilayers with the relatively small intensity ratio of indirect to direct bandgap emission, the acoustic phonons could remarkably assist the intervalley scattering process and smear the valley contrast. While, in other bilayers, which show obvious indirect band gap emission, the indirect optical transition process depletes the phonon mode at Λ point dramatically and results in the anomalously robust valley polarization in bilayer WS₂. These results help recognize the crucial role of electron-phonon coupling on intervalley relaxation in bilayer WS₂ and provide new insights into the future design of valleytronic devices based on two-dimensional TMDs.

Introduction

Two-dimensional (2D) group-VIB transition metal dichalcogenides (TMDs) have generated considerable research

interest in recent years for both fundamental studies and application prospects as a result of their inherent energy gaps and numerous other promising features such as the transformation from the indirect to direct bandgap when approaching the monolayer limit.^{1–9} In particular, semiconducting TMDs with the general expression of MX₂ (M represents Mo or W and X symbolizes S or Se)^{6,10} are considered interesting candidates for achieving valleytronics,^{11,12} one rather interesting field where valley degree of freedom is explored as an information carrier.¹³ In monolayer TMDs, there exist inequivalent and energetically degenerate valleys at K and K' points in the hexagonal Brillouin zone.^{14–16} It has been predicted that interband transitions obey the valley-dependent optical selection rule in non-centrosymmetric monolayer TMDs.^{17–20} More specifically, the direct bandgap transitions at K (K') exclusively couple to σ_+ (σ_-) circularly polarized light.^{6,10} This valley-contrasted circular polarization, together with the large separation between K and K' points in the momentum space, makes valley serve as another robust index of charge carrier in addition to spin.²⁰ Valley polarization could be detected by measuring the circular states of photoluminescence (PL) after selective optical pumping and the expected circular dichroism has been observed in monolayer TMDs in this way.^{14–16,21,22}

In bilayer TMDs with inversion symmetry, the valley-dependent selection rule does not apply anymore and low valley contrast was observed in AB-stacked bilayer MoS₂,^{15,23,24} which greatly restricts the range of thickness selection for achieving potential MoS₂-based valleytronics. In contrast to MoS₂ with comparable spin-valley coupling and interlayer hopping energy, the significantly higher spin-valley coupling strength in bilayer tungsten-based TMDs (WX₂) leads to the suppressed interlayer hopping. Therefore, WX₂ bilayers possess an extra index called layerpolarization in addition to valley and spin indices, which could provide information on the location of charge carriers, either top-layer or bottom-layer.^{14,25} The giant coupling between spin, layer, and valley paves a new way to manipulation of electronic degrees of freedom in WX₂.^{14,25} Excitingly and surprisingly, highly selective circular polarization

^aDivision of Physics and Applied Physics, School of Physical and Mathematical Sciences, Nanyang Technological University, 637371, Singapore

^bKey Laboratory of Chemical Lasers, Dalian Institute of Chemical Physics, Chinese Academy of Sciences, Dalian 116023, China

^cState Key Laboratory of ASIC & System, School of Information Science and Technology, Fudan University, Shanghai 200433, China

^dKey Laboratory of Flexible Electronics (KLOFE) & Institute of Advanced Materials (IAM), Jiangsu National Synergetic Innovation Centre for Advanced Materials (SICAM), Nanjing Tech University (NanjingTech), 30 South Puzhu Road, Nanjing 211816, China

* Address correspondence to yuting@ntu.edu.sg; cxcong@fudan.edu.cn

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has been reported for the direct transition in centrosymmetric bilayer WS₂ and WSe₂,^{14, 26, 27} which is not only contrary to the widely accepted anticipation that valley-induced circular polarization should be inherently absent in centrosymmetric materials, but also shows an even larger valley contrast value than that of the monolayer,^{14, 26} indicating that bilayer WX₂ is an fascinating platform for further exploration of valley physics.¹⁸ However, the unexceptionally large valley contrast in bilayer WX₂ is far from being well understood and deserves further investigation. The anomalous valley property was attributed to either localization of spin polarization in each individual layer by Liu *et al.*²⁸ or suppressed interlayer hopping as a result of large spin-valley coupling compared to interlayer hopping amplitude by Zhu *et al.* in bilayer WX₂.^{14, 25} Though these explanations provide valuable information that valley polarization is not only limited to noncentrosymmetric systems in WX₂, why the valley polarization in bilayer WX₂ could be obviously larger than that in the monolayer counterpart^{14, 27} still cannot be explained from neither one of these two viewpoints and remains to be elucidated.

Interlayer coupling has been shown to significantly tune the optical properties of bilayer WX₂.^{29, 30} However, up to now, the experimental studies of valley properties have been limited to mechanically exfoliated (ME) bilayer WS₂ samples with quite strong interlayer coupling.^{14, 26, 27} Though the interlayer coupling is expected to have pronounced effect on valley polarization,²⁴ systematic studies of their relationship are still lacking in bilayer WX₂. A detailed study of the modulation of the valley polarization by interlayer coupling should help unveil the physics behind the unexpectedly large circular polarization in bilayer WS₂ and provide new insights into the future development of valleytronic devices based on TMDs. In this work, we explore the origin of the anomalously high valley polarization in bilayer WS₂ by a systematic study of samples with different polytypes and on distinct substrates fabricated by different methods. The effect of phonon on valley polarization is clearly revealed by a comparison of valley behaviors in various bilayer WS₂ samples using temperature-dependent circularly polarized PL spectroscopy. Bilayer WS₂ samples whose light emissions are mainly contributed by the direct-gap emission peak possess low-temperature valley contrast similar to the monolayer counterpart as a result of the suppressed interlayer hopping and the acoustic phonons are shown to be the dominant factor to assist the intervalley scattering process. And, the depletion of such phonon in the indirect optical transition process could give rise to the exceptionally robust valley polarization in some WS₂ bilayers, where indirect-gap emission contributes significantly to the overall light emission.

Results and discussion

Before we probe circularly polarized behaviors of bilayer WS₂, we firstly studied the effects of substrate and fabrication method on valley contrast in monolayer WS₂ as a reference. Temperature-dependent circularly polarized PL measurements were conducted on three kinds of monolayer samples, i.e.

chemical vapor deposition (CVD)-grown WS₂ both on sapphire and SiO₂/Si substrates, and ME one on SiO₂/Si substrate. Fig. S1 of the ESI[†] shows the evolution of PL spectra for the three monolayer WS₂ samples from 80 to 300 K. The PL emission of monolayer WS₂ consists of two components corresponding to the direct excitonic transition at K point in the Brillouin zone, neutral exciton (A) at higher energy and trion (A⁻) at relatively lower energy.^{31, 32} Though the relative spectral weights of A and A⁻ may vary for different types of monolayer WS₂ samples, they all share the similar trend of A-A⁻ spectral weight transformation with increasing temperature, which can be explained by the escape of electrons from the trion state owing to thermal fluctuations.^{33, 34} The degree of circular polarization is calculated as²⁶

$$\rho = \frac{I(\sigma_-) - I(\sigma_+)}{I(\sigma_-) + I(\sigma_+)} \quad (1)$$

where $I(\sigma_-)$ or $I(\sigma_+)$ represents the intensity of corresponding circularly polarized luminescence. The valley contrast of A and A⁻ peaks in CVD-grown WS₂ on sapphire substrate is slightly larger than that in the other two samples at 80 K (see Fig. S2 of the ESI[†]), which indicates the trivial effect of substrate and fabrication method on valley contrast in monolayer WS₂.

We then studied the valley behaviors of bilayer WS₂. When two individual layers vertically stack, different bilayer structures can be formed depending on the twist angle ϑ , among which the most stable configurations are AA stacking order when $\vartheta = 0^\circ$ and AB stacking (also called Bernal stacking) sequence when $\vartheta = 60^\circ$.³⁵ To begin with, we compared the valley behaviors of AA- and AB-stacked bilayer WS₂ on SiO₂/Si substrate (Fig. 1). According to the relative orientation of the two vertically stacked layers from the optical images in Fig. 1c and d, the twist angle and the corresponding stacking order can be determined.³⁵ Fig. 1a and b present the circularly polarized components of PL spectra as a function of temperature for AA- and AB-stacked bilayer WS₂. The A peak dominates the PL spectra and redshifts with the increase of the temperature, which is attributed to the reduction of the direct transition energy caused by the expanded in-plane lattice constant.³⁶ As can be seen in Fig. 1e, both of these two samples have similar dependence of valley contrast on temperature and the valley contrast at 80 K is close to that of the monolayer WS₂ on SiO₂/Si substrate. This observation is due to the suppressed interlayer hopping in these two samples. In AB-stacked bilayer WS₂, it is caused by the large spin-valley coupling of holes compared to interlayer hopping amplitude,^{25, 37} while the opposite spin of electrons between neighbouring layers inhibits the interlayer hopping in AA-stacked bilayer WS₂.^{17, 24, 38} By increasing the integration time, the indirect bandgap peak (denoted as I) corresponding to Λ - Γ transition³⁹ could also be observed, as shown in Fig. S3 of the ESI[†]. Though I peak is much broader than the A exciton peak, the integrated intensity of the former is only slightly larger than one quarter of that of the latter, which makes I peak difficult to be resolved under the measurement condition in Fig. 1. Since the polarization of the weak I peak in

Fig. 1 Circularly polarized behaviors of CVD-grown AA- and AB-stacked bilayer WS₂ on SiO₂/Si substrate. Circularly polarized components of PL spectra of as a function of temperature for (a) AA- and (b) AB-stacked bilayer WS₂. (c) and (d) show optical images of AA- and AB-stacked bilayer WS₂ samples, respectively. (e) Temperature dependence of circular polarization for AA- and AB-stacked bilayer WS₂. The excitation light is left-circularly polarized in all the measurements.

bilayer WS₂ on SiO₂/Si substrate is not the focus of this paper, we did not use long integration time for the collection of PL spectra at low temperatures to avoid laser-induced damage.

To investigate the effect of fabrication method on valley contrast in bilayer WS₂, temperature-dependent circularly polarized PL measurements were conducted on ME bilayer WS₂. Fig. 2 shows the circularly polarized behaviors of ME bilayer WS₂ on SiO₂/Si substrate as a function of temperature. Since ME

bilayer WS₂ was exfoliated from a bulk 2H-WS₂ crystal, it is supposed to possess a AB stacking sequence.⁴⁰ As shown in Fig. 2a, the obvious *I* peak appears throughout the whole temperature range and exhibits a blueshift with increasing temperature, consistent with the previous report.³⁶ In contrast to the remarkable valley-polarized behaviors of A exciton, the *I* peak is circularly unpolarized at all the measured temperature conditions, in good agreement with the previous observation.¹⁴ A comparison of Fig. 2c and 1e shows that the valley polarization of A exciton in ME bilayer WS₂ is obviously larger than that of the CVD-grown AB-stacked bilayer WS₂ on SiO₂/Si substrate and can reach 64.3% at 80 K. Considering that ME monolayer WS₂ shows comparable valley polarization to that of the CVD-grown monolayer WS₂, the pure effect of the fabrication method on valley polarization of individual layers can be excluded and intervalley scattering may possibly be weakened by the interlayer coupling in ME bilayer WS₂ on SiO₂/Si substrate.

To probe whether underlying substrate could influence the intervalley scattering, we then measured the circularly polarized behaviors of CVD-grown AA-stacked bilayer WS₂ on sapphire substrate (Fig. 3). As shown in Fig. 3a and b, CVD-grown AA-stacked bilayer WS₂ on sapphire substrate can be classified into two types based on their distinct valley polarization and light emission pattern. For the first kind of samples (marked as AA-1) with relatively large valley polarization (see also Fig. 3e), PL spectra contain obvious contribution of the *I* peak apart from the A exciton peak at high temperatures. In contrast, the *I* peak is much weaker for the other kind of bilayer sample (marked as AA-2) and its valley polarization is close to that of the CVD-grown AA-stacked bilayer WS₂ on SiO₂/Si substrate. Therefore, it could be inferred

Fig. 2 Circularly polarized behaviors of ME bilayer WS₂ on SiO₂/Si substrate. (a) Circularly polarized components of PL spectra of as a function of temperature for ME bilayer WS₂ on SiO₂/Si substrate. (b) Optical image of the ME bilayer WS₂ sample. (c) Temperature dependence of circular polarization for ME bilayer WS₂. The excitation light is left-circularly polarized in all the measurements.

Fig. 3 Circularly polarized behaviors of CVD-grown AA-stacked bilayer WS_2 on sapphire substrate. (a) Circularly polarized components of PL spectra of as a function of temperature for AA-stacked bilayer WS_2 with relatively (a) strong and (b) weak I peak (marked as AA-1 and AA-2, respectively). (c) and (d) show optical images of the two bilayer WS_2 samples corresponding to AA-1 and AA-2. (e) Temperature dependence of circular polarization for these two kinds of AA-stacked bilayer WS_2 samples. The excitation light is left-circularly polarized in all the measurements.

that the valley polarization is associated with the intensity of the I peak. According to the calculated structural energy for WS_2 bilayers with different stacking, there are two possible high-symmetry AA stacking configurations, with the S atoms in the top layer placed above either the W atoms or the S atoms in the bottom layer.²⁹ Due to steric effects, the interlayer distance is different for these two configurations,³⁵ which may result in different interlayer coupling and intensity of the I peak. The varying interlayer coupling strength in different CVD-grown bilayer WS_2 samples will be further discussed later. In addition,

the sharp and strong emission from sapphire substrate appears at around 693 nm⁴¹ in all PL spectra and is circularly unpolarized throughout the whole temperature range. We also conducted the temperature-dependent circularly polarized PL measurement on AB-stacked bilayer WS_2 on sapphire substrate (see Fig. S4 of the ESI[†]), but the signal-to-noise ratio is too low to resolve the valley behaviors due to the vanished interference effect, which fails to enhance the efficiency of light absorption and collection unlike SiO_2/Si substrate.⁴²

Finally, to obtain a comprehensive view of the correlation

Fig. 4 Dependence of circular polarization on the I peak. (a) PL spectra of different types of bilayer WS_2 samples at 300 K. The PL features of sapphire were subtracted in the spectra of bilayer WS_2 on sapphire substrate for clarity. (b) Temperature dependence of circular polarization for different types of bilayer WS_2 samples.

between the valley contrast and I peak, we compared the unpolarized PL spectra at room temperature and the corresponding valley behaviors of different types of bilayer WS_2 samples in Fig. 4. It can be clearly seen that the valley polarization is indeed closely related to the intensity of the I peak in bilayer WS_2 samples (see Fig. 4a and b). More specifically, the bilayer WS_2 samples with the relatively strong I peak have a larger valley contrast than those with the relatively weak indirect bandgap emission. The link can be explained by phonon which plays an important role in both the indirect transition and intervalley scattering process.^{14, 35, 43} The indirect transition in both AA- and AB-stacked bilayer WS_2 occurs between Γ and Λ points^{29, 36} with the assist of Λ -point phonon for the momentum conservations. On the other hand, the intervalley scattering between K and K' points requires the participation of a phonon with the corresponding wave vector difference,⁴³ twice as large as that of the previous one which assists the indirect transition process.¹⁵ Therefore, the existence of relatively strong I peak decreases the possibility of intervalley scattering by depleting phonon which may have participated in this process in pair, leading to the enhanced valley contrast. Among the three bilayer WS_2 samples with the relatively weak indirect-gap emission peak, AA-stacked bilayer WS_2 on sapphire substrate is kind of special and has larger valley contrast than those on SiO_2/Si substrate at low temperature, which is attributed to the inheritance of the valley behaviors of monolayer WS_2 on two substrates (see Fig. S2 of the ESI†). To further confirm the relationship between valley polarization and the I peak, we explored the temperature dependence of valley polarization in five bilayer WS_2 samples. Phonon belongs to Boson and its number at the equilibrium obeys Bose–Einstein statistics. As shown in Fig. 4b, for the bilayer samples which do not show strong I peak, their circular polarization dependence on temperature can be well fitted by Equation 2, which is inversely promotional to phonon population.

$$\rho \propto [\exp(E_p/k_B T) - 1] \quad (2)$$

Table 1 lists the fitted energy and wavenumber of phonons from fitting, together with assignment of phonons based on phonon dispersion of WS_2 .⁴⁴ As discussed previously, the phonon mode at Λ point could work in pair to satisfy the momentum conservation during the intervalley scattering. The three phonon modes at Λ point with the appropriate energy⁴⁴ further

supports our explanation of the high valley polarization in bilayer WS_2 with the relatively strong I peak by phonon depletion in the indirect recombination process. Our finding is in agreement with one recent work on the origin of double-resonance process in TMD.⁴⁵ By probing Raman spectra as a function of the laser excitation energy, Carvalho *et al.* claimed that acoustic phonon dominates the intervalley scattering of electrons and possibly destruct the valley polarization in MoS_2 .⁴⁵ On the other hand, for the bilayer samples with the relatively strong I peak, the change of circular polarization degree versus temperature, especially the values in the low temperature range as marked in Fig. 4b, cannot be fitted well by this expression. This is because phonon is partly depleted in the indirect transition process and the effective number of phonons which can assist the intervalley scattering does not obey Bose–Einstein statistics anymore.

From Fig. 4a, it should also be noticed that both the peak position and width vary for the PL spectra of different types of bilayer WS_2 samples. The redshift of the I peak in AA-stacked bilayer WS_2 compared with ME bilayer WS_2 is due to the lower energy of indirect transition for AA-stacked bilayer WS_2 according to theoretical calculation.²⁹ For the A exciton peak, the relative shift is attributed to the combined effect of interlayer coupling and local strain induced by the sample–substrate interactions. A comparison of PL spectra for the samples on the same substrate (i.e. ME versus CVD-grown AA/AB-stacked bilayer WS_2 on SiO_2/Si and CVD-grown AA-1 versus AA-2 bilayer WS_2 on sapphire) demonstrates that the energies of the A exciton peak for bilayer WS_2 with the relatively stronger I peak generally redshift compared to those with the weak indirect-gap emission peak. The weak I peak manifests the relatively weakened interlayer coupling and therefore the peak positions of the A exciton for bilayer WS_2 with the relatively weak indirect-gap emission peak exhibit blueshifts towards those of monolayer WS_2 at higher energies.^{39, 46} To further confirm that the shift is indeed caused by interlayer coupling, we compared the frequency differences of $E_{2g}^1(\Gamma)$ and $A_{1g}(\Gamma)$ modes in different types of bilayer WS_2 samples on SiO_2/Si substrate, which are indicative of the interlayer coupling strength.^{35, 47} As shown in Fig. S5 of the ESI†, the separation of $E_{2g}^1(\Gamma)$ and $A_{1g}(\Gamma)$ modes is larger in ME bilayer WS_2 than those of CVD-grown bilayer counterparts, which demonstrates

	E_p (meV)	ω_p (cm^{-1})	Assignment
CVD AA on SiO_2	17.13	138.1	ZA (Λ)
CVD AB on SiO_2	19.15	154.5	LA (Λ)
CVD AA on sapphire (without strong I peak)	12.55	101.2	TA (Λ)

Table 1. The energy, wavenumber, and assignment of the phonons that participate in the intervalley scattering of electrons for different types of bilayer WS_2 samples.

the stronger interlayer coupling in the ME sample and provides support for our explanation of the exciton shift for samples on the same substrate from the viewpoint of interlayer coupling. The distinct strength of interlayer coupling is attributed to the change of interlayer distances in different types of bilayer WS_2 samples since van der Waals interaction is negatively related to the interlayer distances.^{35, 48} In contrast to the ME bilayer WS_2 sample, the uncontrollable variation of the interlayer distance in different types of CVD-grown bilayer samples could lead to the varying interlayer coupling strength.³⁵ Future work will investigate the underlying cause of the varying interlayer coupling strength in different CVD-grown bilayer WS_2 samples, even on the same sapphire substrate. Moreover, for the same kind of bilayer WS_2 samples (i.e. bilayer WS_2 with either strong or weak I peak) on different substrates, the relative shift of the A exciton peak might be due to the local strain induced by the sample–substrate interactions during the exfoliation or growth process, which has been commonly observed in atomically thin layered materials.^{49–54} The lower surface roughness of sapphire compared to SiO_2 ⁴⁹ makes the conformally adhered bilayer WS_2 on it subject to smaller tensile strain and leads to the higher energies of the exciton peak for bilayer WS_2 on sapphire substrate.^{32, 55} This is consistent with our observation of the exciton redshift in ME (CVD-grown AA/AB-stacked) bilayer WS_2 on SiO_2/Si substrate relative to the CVD-grown AA-2 (AA-1) counterpart on sapphire substrate. Furthermore, it is known that the exciton-phonon interactions broaden linewidths of excitons.⁵⁶ For the variation of exciton width as shown in Fig. 4a, the ME and CVD-grown AA-1 bilayer WS_2 have broader A exciton peaks than other bilayer samples, which reflects the stronger exciton-phonon interaction in these two types of samples.

Experimental section

Monolayer and bilayer WS_2 samples were fabricated by mechanical exfoliation and grown by the CVD method, followed by temperature-dependent circularly polarized PL measurements.

Sample preparation: CVD monolayer and bilayer WS_2 sample were grown on 300 nm SiO_2/Si and sapphire substrates by the previously reported technique.⁵⁷ Compared with the experimental process to grow monolayer WS_2 , the growth time under 750 °C was increased for bilayer WS_2 , which could make the vertical layer-by-layer growth more preferable.³⁵ The exfoliated WS_2 flakes used in this work were obtained by mechanical cleavage of a bulk 2H- WS_2 crystal (2D Semiconductors, CAS #12138-09-9, USA) and then transferred onto 300 nm SiO_2/Si substrates. Monolayer and bilayer WS_2 flakes were selected by optical microscope (Olympus BX 51), followed by confirmation through PL/Raman spectroscopy.

Optical characterization: The PL measurements were performed with a WITec CRM200 Confocal Raman system under 532-nm excitation laser with 150 lines/mm grating. To achieve polarization-resolved PL measurements, the linearly polarized light was firstly transformed to left-circularly

polarized one by passing through an achromatic quarter-wave plate (WPQ10M-532, Thorlabs) and then shone on the sample. Next, the emitted backscattering beam comprising both left- and right-circularly light got through the same quarter-wave plate and was separated into two perpendicularly polarized beams, which could be separately detected by rotating the linear polarizer located on top of the edge filter. The accuracy of circular polarization degree for our setup was no less than 94.0%. The linear polarizer was rotated cautiously to avoid any perturbation effect on the collimation of the whole system throughout the experiment. After both left- and right-circularly polarized components of PL spectra were measured, the linear polarizer was rotated back to the original position to confirm that the measured spectrum was fully reproducible. To achieve a fair comparison by ruling out the hysteresis effect, all temperature-dependent PL measurements were conducted from room temperature down to 80 K. The cooling of the samples was realized by a temperature controlled stage HFS600E (Linkam Scientific Instruments). At each temperature, at least two different points were tested to confirm that the observed trend of the spectral change was typical. A long-working distance 50× objective lens was used in all the PL measurement with numerical aperture of 0.55. Raman measurements were carried out by the same WITec system under the excitation sources of 532 nm laser with 1800 grooves/mm gratings at room temperature. The laser spot was evaluated to be around 1 μm . The laser power at the sample surface was maintained with great care to avoid laser-induced damage and kept unchanged during the temperature-dependent measurement.

Conclusions

In summary, we have investigated temperature-dependent valley polarization in various AA- and AB-stacked bilayer WS_2 samples and experimentally demonstrated the correlation between the intensity of the indirect bandgap emission and valley polarization. We showed that acoustic phonons play a leading role in the valley polarization of bilayer WS_2 and the depletion of such phonon in the indirect optical transition process could contribute to the exceptionally robust valley polarization. Our results shed lights on the critical role of electron-phonon coupling on intervalley scattering process in bilayer WS_2 and lay a foundation for developing valleytronics applications exploiting the strong electron-phonon interaction in 2D TMDs. Our findings provide new insights into the realization of more robust valley polarization in broader 2D systems by manipulating the indirect optical transition and intervalley scattering.

Conflicts of interest

There are no conflicts to declare.

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